

ABSTRACT

A memory cell and a method for manufacturing the memory cell. The memory cell is constructed so that it has a ratio of a dimension in the direction of the bit lines to a dimension in the direction of the word line of less than one. The bit lines are formed from the first metallization system of the memory cell, which is the metallization system nearest the surface of the substrate and the silicide regions of the memory cell. The word line is formed from a metallization system above the first metallization system. Thus, the bit lines are positioned vertically between the substrate surface and the word line.